

ABSTRACT OF THE DISCLOSURE

A semiconductor light-receiving device includes:
a semi-insulating substrate; a semiconductor layer of a
first conduction type that is formed on the semi-
5 insulating substrate; a buffer layer of the first
conduction type that is formed on the semi-insulating
substrate and has a lower impurity concentration than
the semiconductor layer of the first conduction type; a
light absorption layer that is formed on the buffer
10 layer and generates carriers in accordance with
incident light; a semiconductor layer of a second
conduction type that is formed on the light absorption
layer; and a semiconductor intermediate layer that is
interposed between the buffer layer and the light
15 absorption layer, and has a forbidden bandwidth within
a range lying between the forbidden bandwidth of the
buffer layer and the forbidden bandwidth of the light
absorption layer.

20